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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/049,885	06/04/2002	Richard Allan Tuck	670-1006	6321
23644	7590	09/23/2004	EXAMINER	
BARNES & THORNBURG P.O. BOX 2786 CHICAGO, IL 60690-2786			SANTIAGO, MARICELI	
			ART UNIT	PAPER NUMBER
			2879	

DATE MAILED: 09/23/2004

Please find below and/or attached an Office communication concerning this application or proceeding.



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APPLICATION NO./ CONTROL NO.	FILING DATE	FIRST NAMED INVENTOR / PATENT IN REEXAMINATION	ATTORNEY DOCKET NO.
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EXAMINER

ART UNIT	PAPER
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20040809

DATE MAILED:

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Commissioner for Patents

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a fax communication submitted by William M. Lee on August 18, 2004.

The application has been amended as follows:

In the specifications,

Page 12, lines 13-14, please delete the text:

"in which Figures 1 to 3 have already been mentioned above and,".

Page 12, line 15, insert the following text:

--Figures 1a and 1b show the structure of a cathode plane;

Figure 2a shows a typical structure of an emitter;

Figure 2b shows an exemplary case where an emitter with 2 micron particles is used in an 8 micron diameter emitter cell fabricated in a nominal 4 micron thick gate insulator;

Figure 3a, 3b and 3C illustrate a technique that involves forming a gated structure with a gate electrode deposited on a silicon dioxide layer that is grown on a conductive silicon substrate;--.

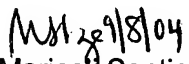
Art Unit: 2879


Contact Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mariceli Santiago whose telephone number is (571) 272-2464. The examiner can normally be reached on Monday-Friday from 9:30 AM to 6:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nimesh Patel, can be reached on (571) 272-2457. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).


Mariceli Santiago
Patent Examiner
Art Unit 2879


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